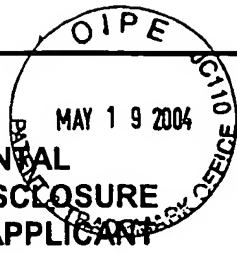


PTO/SB/08A

**SUPPLEMENTAL
INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

**Complete if Known**

Application Number	10/705,813
Filing Date	November 10, 2003
Confirmation Number	5409
First Named Inventor	Milind Kulkarni
Group Art Unit	1765
Examiner Name	Not Yet Assigned
Attorney Docket No.	MEMC 02-0201 (3035.1)

Sheet 1 of 2

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code ² (if known)		
/	51	5,137,699		Azad	08-11-1992
	52	6,036,776		Kotooka et al.	03-14-2000
	53	6,159,438		Iida et al.	12-12-2000
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FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	T ⁶
		Office	Number ⁴	Kind Code ² (if known)			
/	57	EP	1 158 076	A1	Komatsu Denshi Kinzoku Kabushiki Kaisha	11-28-2001	
	58	JP	63-008291		Seiryu Eng. Co. Ltd.	01-14-1988	A
	59	JP	06-027684		Tokyo Ohka Kogyo Co. Ltd.	02-04-1994	A
	60	JP	11-043396		Nittetsu Denshi KK	02-16-1999	A

Examiner Signature

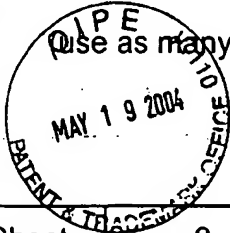
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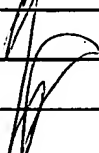
12/23/05

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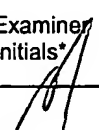
¹Unique citation designation number. ²See attached Kinds of U.S. Patent Documents. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to place a check mark here if English language Translation is attached or place an "A" here if English language abstract is attached.

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				Group Art Unit	1765
				Examiner Name	Not Yet Assigned
Sheet	2	of	2	Attorney Docket No.	MEMC 02-0201 (3035.1)

	61	JP	11-25557		Mitsubishi Materials Silicon Corp.	09-21-1999	A
	62	WO	01/21861	A1	MEMC Electronic Materials, Inc.	03-29-2001	
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OTHER ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ⁶
	64	International Search Report, PCT/US03/36046, dated April 21, 2004, 8 pages	


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Sheet	3	of	4	Attorney Docket No.	MEMC 02-0201 (3035.1)

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	34	JP	96268794	A	Sumitomo Sitix Corporation	10-15-1996	✓

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Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
	35	ABE, T., et al., "Etch Pits Observed in Dislocation-Free Silicon Crystals", <i>Japan J. Appl. Phys.</i> , 1966, Pages 458-459, Volume 5	
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	44	SHIMURA, F., "3.4.1 Point Defects", <i>Semiconductor Silicon Crystal Technology</i> , 1989, Pages 55-60, Academic Press, Inc., California	
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	46	SRIVASTAVA, R.K., et al., "Interface Shape in Czochralski Grown Crystals: Effect of Conduction and Radiation", <i>Journal of Crystal Growth</i> , 1985, Pages 487-504, Volume 73, North-Holland Publishing Company, Amsterdam	
	47	VIRZI, A., "Computer Modelling of Heat Transfer in Czochralski Silicon Crystal Growth", <i>Journal of Crystal Growth</i> , July 1991, Pages 699-722, Volume 112, Number 4, North-Holland Publishing Company	
	48	VORONKOV, V.V., et al., "Point Defects in Silicon Crystal Growth", <i>ECS Proc.</i> , 2001, Pages 3-18, Volume 2001-29, presented at the DECON Symposium 2001	
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